Maze Mouse

by

Nurin Naurah bt. Md. Yusof

Dissertation submitted in partial fulfillment of the requirements for the Bachelor of Engineering (Hons) (Electrical & Electronics Engineering)

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CERTIFICATION OF APPROVAL

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A project dissertation submitted to the Electrical & Electronics Engineering Programme Universiti Teknologi PETRONAS in partial fulfillment of the requirement for the Bachelor of Engineering (Hons) (Electrical & Electronics Engineering)

Approved:

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Dr. Nordin bin Saad Project Supervisor

UNIVERSITI TEKNOLOGI PETRONAS TRONOH, PERAK

June 2004

CERTIFICATION OF ORIGINALITY

This is to certify that I am responsible for the work submitted in this project, that the original work is my own except as specified in the references and acknowledgements, and that the original work contained herein have not been undertaken or done by unspecified sources or persons.

Nurin Naurah bt. Md. Yusof

ABSTRACT

This report is intended to provide an insight view of the Maze Mouse project. The first chapter serves as the introduction to the project, which covers the background of study, problem statement, and objectives and scope of study. The objective of this project is to produce a prototype of a mouse that can find its own way out of a maze smoothly, but not necessarily very quickly. This will be explained later in the report. This project requires strong basics in electronics, covering three important aspects of the mouse which are microcontroller, infrared sensor and stepper motor. The earlier part of the second chapter describes the details of the Sterling Mouse, an example of a maze mouse. The Sterling Mouse was created by Nick Smith as a participant in the Micromouse Competition held in the United States. The third chapter of this report presents the methodology used in completing this Maze Mouse project. This includes the purchasing and procurement of the components, circuit construction, programming and integration of the mouse's separate circuits. In the next chapter, you will be provided with the details of the project work, which focuses on how the prototype gets to work.

ACKNOWLEDGEMENTS

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TABLE OF CONTENTS

ACKNOWLEDGEMENTS
LIST OF TABLESix
LIST OF FIGURES
CHAPTER 1 INTRODUCTION 1
1.1 Background of Study1
1.2 Problem Statement
1.3 Objectives and Scope of Study
CHAPTER 2 LITERATURE REVIEW AND/OR THEORY
2.1 [2]Sterling Mouse by Nick Smith
2.1.1 Mouse Mechanics
2.1.2 Computer
2.2 Microcontroller
2.3 Infrared Sensor
2.3.1 Common-Emitter Amplifier Circuit9
2.3.2 Common-Collector Amplifier Circuit
CHAPTER 3 METHODOLOGY OR PROJECT WORK 14
3.1 Literature Review14
3.2 Hardware Construction
3.2.1 Microcontroller Circuit
3.2.2 Motor Driver Circuit
3.2.3 Infra Red Sensor Circuit
3.3 Software
CHAPTER 4 RESULTS AND DISCUSSION
4.1 Microcontroller circuit
4.2 Infrared Sensor
4.2.1 Maze Mouse Sensor Circuit
4.3 Motor Driver
4.4 The Maze
4.5 Programming
CHAPTER 5 CONCLUSION
REFERENCES

APPENDIX A	
APPENDIX B	
APPENDIX C	
APPENDIX D	
APPENDIX E	

LIST OF TABLES

Table 1 The chips used in the brain of the Sterling Mouse	8
Table 2 Infrared Specifications Definition	12
Table 3 Differences between servo motors and stepper motors	16
Table 4 Inputs from sensors and the corresponding actions	24

LIST OF FIGURES

Figure 1 Overall structure of the Sterling Mouse	6
Figure 2 Mechanical diagram of the Sterling Mouse	7
Figure 3 Common-Emitter Amplifier	10
Figure 4 Common-Collector Amplifier	10
Figure 5 Detector Shielding Method	13
Figure 6 Microcontroller board layout	
Figure 7 Circuit diagram of an 80C31 with an external program memory	19
Figure 8 Infrared sensor circuit board	20
Figure 9 Sensor circuit of the Maze Mouse	21
Figure 10 Motor driver circuit board layout	22
Figure 11 Movements of the mouse along the maze	23
Figure 12 Example of a maze and the projected path of the mouse	23
Figure 13 General flowchart of the mouse's operation	25

CHAPTER 1 INTRODUCTION

1.1 Background of Study

The Maze Mouse is a subject already popular in countries such as the United States of America (USA), United Kingdom (UK), Japan and Canada. There have been a number of Maze Mouse projects done by university students from these countries. There have also been a few micromouse competition being held overseas, in which the concept is similar to my maze mouse. The competitions are held in a large-scale manner, in which they involve contestants from different institutions.

A maze mouse is actually a small robot which is designed to solve a given maze in which it is placed. However, the detailed specifications of each mouse depend on the requirement. For example, a maze mouse must have the ability to solve a maze in the shortest time in order to win a competition. As for my mouse, the requirement is different as would be described later. Development of the robot involves both the physical construction of the robot and the realization of maze solving ability by implementing some maze-solving algorithms in software.

Based on the information gathered, a maze mouse basically consists of three major parts:

i. Mouse control

This is the most crucial part, since it handles sensor information and motor control in pursuit of solving a given maze. Various types of controller can be used for a maze mouse. Current applications show that the type ranges from simple PLC control to more complex neuro-fuzzy technique.

ii. Sensor

There are a few types of sensors which have been used in previous maze mouse projects, such as micro switch sensor, relay sensor and infra-red sensor. These sensors are responsible to provide information (e.g. junctions or dead ends) about the path followed to the controller. It is based on these sensor inputs that the mouse controller can perform the maze solving algorithm.

iii. Motor driver

This part controls the motor speed and direction of the mouse while moving along a given maze. This part is important to ensure smoothness of the mouse's movement. The project work regarding this part requires some mechanical knowledge.

Apart from these three parts of the mouse, another important element of the mouse is the power supply part. Most of the time, the mouse gets its power supply from a 9V battery.

The software part of the mouse involves the programming of the microcontroller, RAM and/or ROM. The program plays the most important role in determining a successful operation of the mouse. It contains the predefined algorithm that the mouse should follow in order to get out of the maze safely.

Together with the prototype of the mouse, the maze is not to be left out. Usually, the mazes used in the micromouse competitions are made from wood and they follow certain standard as defined by the rules of the competition. Similarly, the maze for this project will be constructed according to a set of criteria that will be discussed in later chapters.

1.2 Problem Statement

By the end of the year, a prototype of a maze mouse is to be produced. The maze mouse must be able to find its own way out of a given maze, regardless of the time consumed and the distance traveled. The maze is to be built using black and white paints to differentiate between the walls and maze, respectively.

The project is to be carried out based on two different but highly related aspects: hardware and software. The hardware aspect requires the development of the microcontroller circuit, sensor interfacing and the mouse mechanical system. These three elements should then be integrated so as to produce a complete prototype.

The software aspect of the project will require the development of a program that controls the whole operation of the mouse. Based on the information from the sensors, the program must be able to come out with the decision for the mouse to act. Specifically, programs are to be written for the 80C31 microcontroller, the RAM IC and the EPROM IC. In order to write the program, the flow chart of the mouse's movement should first be determined. By the end of the year, the mouse prototype should be able to maneuver and find its route out of the maze.

The maze mouse, and other similar devices, is a very useful tool in the robotics and industrial automation field. It can be used to help us humans in reaching those areas in plants or factories which are either dangerous or within our arms' reach. The basic concept of the maze mouse has also been expanded to produce the Autonomous Guided Vehicle (AGV), an emerging technology at present.

The main principle of AGV, robot navigation, is defined as [1]the guiding of a mobile robot to a desired destination or along a desired path in an environment characterized by a terrain and a set of distinct objects, such as obstacles and landmarks. The autonomous navigate ability and road following precision are mainly influenced by its control strategy and real-time control performance.

By autonomous robot navigation, we mean the ability of a robot to move purposefully and without human intervention in environments that have not been specifically engineered for it. Autonomous navigation requires a number of heterogeneous capabilities, including the ability to execute elementary goalachieving actions, like reaching a given location; to reach in real time to unexpected events, like the sudden appearance of an obstacle; to determine the robot's position; and to adapt to changes in the environment.

1.3 Objectives and Scope of Study

The completion of the project should fulfill these following objectives:

- 1. To understand and construct a fully operational infra-red sensor circuit. This sensor circuit should be able to detect the presence or absence of wall at the left, front or right side of the mouse.
- 2. To understand and construct the motor driver circuit. This circuit is responsible in determining the motor's speed and direction.
- 3. To understand and develop the controller circuit of the mouse, complete with its program, which is the primary element of the mouse. This controller should be able to read the information given by the sensors correctly in order to produce the decision, on which the motor should act, for the mouse to get out of the maze safely.
- 4. Finally, to integrate all the components of the mouse to produce a complete prototype of the maze mouse that can find its own way out of a maze.

This Maze Mouse project will in the end enables me to apply all the technical knowledge learned during the years in the university. This would especially refer to the electronics and programming stuff. Lessons acquired from subjects such as Analogue Electronics and Microprocessor I would be very useful in completing this project.

For the purpose of ensuring the feasibility of the project within the scope and time frame, focus is concentrated mainly on the hardware assembly of the mouse prototype during the first semester. Then, during the second semester, more effort is put into developing the program for the microcontroller. Shown in the Appendix is the Gantt chart of this project's scheduling for two semesters.

CHAPTER 2 LITERATURE REVIEW AND/OR THEORY

2.1 [2]Sterling Mouse by Nick Smith

The Sterling Mouse is one of the contestants for the Micromouse UK competition (Micromouse). Micromouse is an annual robotics competition in which autonomous robot 'mice' compete against each other to solve a 16 by 16 inch maze in the shortest time. Each square of the maze is 18 cm by 18 cm. The walls are 5 cm high and 1.2 cm thick.

The mice participating in the competition can be as simple as a Lego Mindstorms kit with light and touch sensors, or as complex as a vision guided chassis with DC motors controlled by a Digital Signal Processing chip.

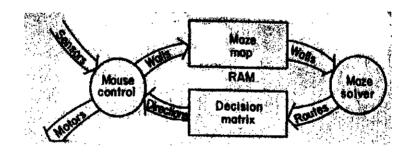


Figure 1 Overall structure of the Sterling Mouse

The overall structure of the Sterling Mouse is as illustrated above. It can be seen that there are basically two independent parts. The mouse control handles sensor information and motor control and builds up a bit map of the maze. The maze solver takes the bit map of the maze and builds a decision matrix on which the mouse acts.

2.1.1 Mouse Mechanics

Although described as circular, the mouse is actually octagonal with a driving wheel on each side. It also has a cup mounted ball bearing for stability and ease of movement at the front and back. A pair of stepper motors (one for each wheel) drives the main wheels under direct CPU control. To get a good top speed the motors are accelerated from rest using an acceleration table derived by trial and error. Direction control is achieved in a tank-like manner by accelerating and decelerating the wheels independently. Turning is accomplished by reversing one of the wheels. The mouse has eight switches to enable different speed ranges to compensate for actual conditions on the day and also variable battery power.

The position of the mouse is calculated by keeping a tally of the number of steps moved over time. To allow for cumulative errors and the possibility of the motors dropping some steps the mouse position is reset whenever a wall is encountered in front or whenever a wall disappears on either side, i.e. about half way between two squares. A maximum error of about five inches can be tolerated.

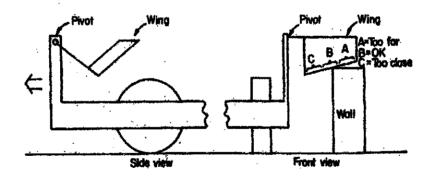


Figure 2 Mechanical diagram of the Sterling Mouse

There are seven sensors in total: one microswitch on the front and three sensors built from old relay contacts mounted on wings on each side. The wings, shown in Figure 2, essentially tell the mouse whether there is a wall present and if so whether the mouse is too close or too far from it on each side. The mouse will run down the centre of the maze, within a fixed tolerance, as long as at least one side wall is present. When there are no walls on either side the mouse travels in a straight line.

2.1.2 Computer

The brain of the mouse is made up of the six chips detailed below:

MANUFACTURER	FUNCTION NO.	DESCRIPTION	
RCA CDP	1802	CPU (CMOS)	
RCA CDP	1851	Programmable I/0 interface (CMOS)	
RCA CDP	1859	Memory management chip (CMOS)	
RCA	4069	Hex inverter (CMOS)	
Mostek	4118 1 k x 8 static RAM		
Hitachi	2716	2k x 8 5 V PROM	

Table 1 The chips used in the brain of the Sterling Mouse

The requirement of low power consumption makes the use of CMOS chips highly desirable. Unfortunately space limitations and the need for hand wiring precluded the use of the lower density CMOS memories.

Maximum use of the 1802 CPU has enabled a powerful program to be produced using little memory. The 1802 has 16 x 16-bit internal registers and all mouse status and control information is kept in these registers. Only 1 byte of RAM is required, and is used for logic and arithmetic operations. The 16 x 16 byte map of the maze and the 16 x 16 byte decision matrix are also held in RAM. Total EPROM requirements are about 800 byte made up of 700 bytes for the main control program and 100 bytes for the maze solver.

2.2 Microcontroller

Nowadays we can find microcontroller in almost every electronic device such as VTR's, TV's, heating control etc. [3]By using a microcontroller in a hardware design, the workflow is completely different. Most of the time is spent in writing software but on the other hand we can reduce the hardware design to a maximum.

A typical microcontroller device is the 8051 designed by INTEL. In the last 10 years a lot of companies like Atmel, Philips, Matra Harris, OKI, Dallas, Cypress and Infineon have developed new derivates, with special features, all based on the 8051 core. The 8051 is currently the most successful microcontroller family in the world. Software resources are also available without any problems.

2.3 Infrared Sensor

The wavelength range for light in the near infrared region is about [4]700 nanometers (nm) to 1100 nm. The infrared detector, or phototransistor, can be made up fundamentally based on two configurations: common emitter amplifier and common collector amplifier.

2.3.1 Common-Emitter Amplifier Circuit

The common-emitter amplifier circuit (Figure 3) generates an output which transitions from a high state to a low state when light in the near-infrared range is detected by the phototransistor. The wavelength range for light in the near infrared region is about 700 nanometers (nm) to 1100 nm. The output is created by connecting a resistor between the voltage supply and the collector pin of the component. The output voltage is read at the terminal of the collector. It is called an amplifier circuit because the current generated in the component when light is detected is very small. However, the component has an internal amplifier (in this case a phototransistor) which magnifies this current to useful levels.

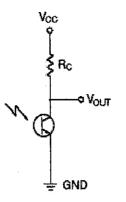


Figure 3 Common-Emitter Amplifier

2.3.2 Common-Collector Amplifier Circuit

The common-collector amplifier (Fig. 2) generates an output which transitions from a low state to a high state when IR light is detected by the phototransistor. The output is created by connecting a resistor between the emitter pin of the component and ground. The output is read at the emitter terminal.

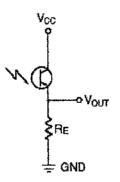


Figure 4 Common-Collector Amplifier

In both circuits the phototransistor can be used in two modes, an active mode and a switch mode. Operating in the active mode means that the phototransistor generates a response proportional to the light received by the component up to a certain light level. When the amount of light surpasses that level, the phototransistor becomes saturated and the output will not increase even as the light level increases. This mode is useful in applications where it is desired to detect two levels of inputs for comparison. Operating in the switch mode means that the phototransistor will either

be "off" (cut-off) or "on" (saturated) in response to the light. This mode is useful when a digital output is required for object detection or encoder sensing.

By adjusting the load resistor in the amplifier circuit one can set the mode of operation. The correct value for the resistor can be determined by the following equations:

Active Mode: $V_{CC} > R_L x I_{CC}$ Switch Mode: $V_{CC} < R_L x I_{CC}$

Typically a resistor value of $5k\Omega$ or higher is adequate to operate the phototransistor in the switch mode. The high level output voltage in the switching mode should equal the supply voltage. The low level output voltage in the switching mode should be less than 0.8 Volts.

The greatest distance at which an infrared solution will still work depends much on the application. [5]In most cases, by pulsing the emitter with a high drive current and using a sensitive photo sensor, such as a photo Darlington, one can expand the range:

- The range for detecting an object by reflection can be from 0 mm to 400 mm. The factors involved are the configuration and reflectivity of the reflective surface, the drive current of the emitter, and the photo sensor output. Dust, however, can impair this range.
- Object sensing by transmissivity (i.e. breaking a beam of light between two points with an object) has a range of 0 to 12 m. The factors involved are the size of the object used to break the beam, the drive current of the emitter, the output type of the photo sensor, and the electrical timing techniques used such as synchronous detection.
- For pure data transmission, the range is from 0 to 15 m. The factors are the data rate, the coding and modulation technique, and the expected signal to noise ratio or bit error rate. A high emitter drive current can improve the range of the system.

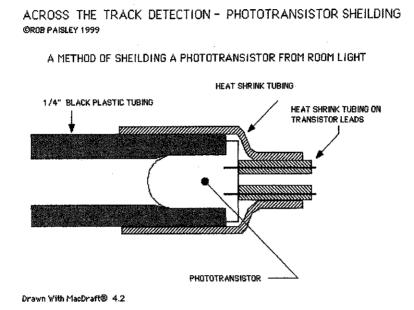
[6]Listed below are the specification definitions for an infrared:

NO.	TERM	DEFINITION
1	Aperture Width	Width of the built-in openings in front of the emitter and photo sensor that define the size of the beam.
2	BV _{CEO>}	Collector-Emitter Breakdown Voltage with the base open.
3	Emission Angle @ 1/2 Power	Angle of the cone where the light intensity is half that on the optical axis.
4	Icc Supply Current	Current drawn from the supply at a given voltage.
5	I _{CEO}	Collector-Emitter current for radiant sensitive devices when the base is open and without radiant incidence.
6	I _F	Current flowing through a diode from anode to cathode.
7	I _{F+}	Diode forward current (I_F) required to cause the output to turn on.
8	I _{F-}	Diode forward current (I_F) required to cause the output to turn off.
9	I _R	Current flowing through a diode from cathode to anode.
10	I _R (D)	Reverse dark current for a given supply voltage.
11	Lead Spacing	Distance between the leads from the emitter side of the package to the photo sensor side.
12	Light Current	Current which flows through a device due to radiant incidence.
13	Negative Threshold	Amount of incident light at which the device turns off.
14	On-State Collector Current	Collector current at a specified radiant incidence and a specified collector voltage.
15	Operating Supply Voltage	Voltage under which the device operates.
16	Output Configuration	Output circuit and function.
17	Output Power	The radiant intensity of emitted light measured in mW/sr.
18	Positive Threshold	Amount of incident light required to turn the device on.
19	Reception Angle @ 1/2 Power	Angle of the cone where the sensitivity is half that on the optical axis.
20	V _F	Voltage between anode and cathode at a specified forward current.
21	V _R	Voltage between cathode and anode at a specified reverse current.

Table 2 Infrared Specifications Definition

[7]Infrared phototransistors are also sensitive to visible light and therefore will need to be shielded in someway to prevent the device from being swamped by the rooms lighting. This can be done by hiding the phototransistor inside a line side structure or placing it inside a short piece of opaque tubing. If the phototransistor is mounted, the back of the transistor can be painted black to prevent room light from entering.

The next diagram shows a method of shielding the detector phototransistor from room light.





CHAPTER 3 METHODOLOGY OR PROJECT WORK

3.1 Literature Review

The project work is first conducted by performing extensive literature review on all topics related to maze mouse. The objective is to gain as much information as possible that is helpful throughout the process of completing the project. The findings are as stated in the previous chapter.

3.2 Hardware Construction

Having understood the concepts of a maze mouse, the next step is to determine the correct circuit to build it. Upon having the circuits, I began the procurement of the required components for the prototype. The list of the hardware components used is in the appendix.

Then, the project work continues with the construction of the circuitries involved to operate the maze mouse. The circuits used to realize the maze mouse are as shown in the appendix.

As stated earlier, the prototype of the maze mouse consists of the following three main circuits:

- i. Microcontroller circuit
- ii. Motor driver circuit
- iii. Infrared sensor circuit

14

Among all the above circuits, the sensor circuit is identified to be the most complex. Therefore, it is first constructed on a piece of breadboard so that its functionality can be tested, independently. This is to ensure correct operation of the sensor to avoid further problems in the future.

The next section will further describe all the three circuits involved.

3.2.1 Microcontroller Circuit

The microcontroller circuit is by heart the most important component of the maze mouse. Basically, the microcontroller coordinates the task of position monitoring, movement, maze navigation and solution evaluation of the mouse. The circuit construction is carried out first before the microcontroller is programmed.

3.2.2 Motor Driver Circuit

As for the motor to be used on the maze mouse, there are two options available: stepper motor and servo motor. Stepper motors are permanent magnetic motors that 'step' one increment each time the computer gives its control electronics one pulse. They do not require position feedback if run within their limits. When stopped, they inherently hold their position.

Servo motors are standard DC or brushless motors with an encoder feedback loop. The computer reads the position of the motor and controls the power applied to the motor.

Stepper motors are generally just as accurate as servos and are simpler and more reliable and maintenance free in harsh dusty applications. The servo motor's encoder is susceptible to dirt and vibration that can cause problem.

For this maze mouse, stepper motors are chosen since they provide precise position control but little speed, whereas DC motors are the opposite. The accurate control can be very handy when trying to measure the position of the mouse. This is because the stepper motors are directed to turn a set arc, not move at a set speed. [8]Table below shows the difference in characteristics between servo motors and stepper motors:

MOTION CHARACTERISTICS	SERVO MOTORS	STEPPER MOTORS
High Torque, Low Speed	Can be considered if cost or complexity is not an issue.	Continuous duty applications requiring high torque and low speed.
High Torque and high speed (>2000 rpm)	Continuous duty applications requiring high torque and high speed. A DC servomotor can deliver greater continuous shaft power at high speeds compared to steppers. High speed up to 12000 rpm is possible. AC servo motors can handle higher current surges compared to DC servos. You can get lot stronger AC servo compared to either DC servo or DC stepper.	If speeds are less than 2000 rpm stepper may be economical. Stepper becomes buiky at high torque.
Short, Rapid Repetitive Moves	Use servo if high dynamic requirements are needed.	Stepper motor will offer more economic solution when requirements are more modest.
Positioning Applications	Servo can handle effectively when load is mostly inertia instead of friction. The ability to overdrive servo motor in intermittent duty allows a smaller motor to be used. If positioning is critical in micron level use servo.	Use stepper motor if torque is lower than 500 oz-in, less 2000 rpm, low to medium acceleration rates.
Applications in Hazardous Environments	Use brushless servo motor.	Use stepper motor.
Low Speed, High Smoothness	Use DC servo.	Use micro stepping.
Control Method	Closed loop.	Preferred to be used in open loop applications.

Table 3 Differences between servo motors and stepper motors

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3.2.3 Infra Red Sensor Circuit

The infra red sensors are used to detect the existence of boundaries in front of it, to the left or to the right of it. Three sensors will be at the left and right side and another two will be at the front side. The sensor circuit is tested repeatedly for its sensitivity and reliability to prevent future problems after a full prototype is developed:

All the hardware required to realize the above circuits are listed in the appendix.

3.3 Software

The software part of this project involves the programming of the microcontroller, Random Access Memory (RAM) and Erasable Programmable Read Only Memory (EPROM) integrated circuits (IC). These IC's are used in the microcontroller circuit of the maze mouse. For the 80C31 microcontroller, the programming will be done using the assembly language.

A lot of programming languages are available for the 8x51 family. [9]Examples are such as PLM51, C51, BASIC, PASCAL or ASSEMBLER. For generating a program which can be executed by a microcontroller, regardless of which language to be used, a compiler is needed. The job of a compiler is to convert a source code, written in a high level language, into machine code. The machine code will be a format which can be executed by a microcontroller and it is possible to be written into an EPROM. The format needed for the 8x51 family will be the INTEL HEX code.

CHAPTER 4 RESULTS AND DISCUSSION

4.1 Microcontroller circuit

Shown below is the rough layout of the microcontroller circuit board of the Maze Mouse:

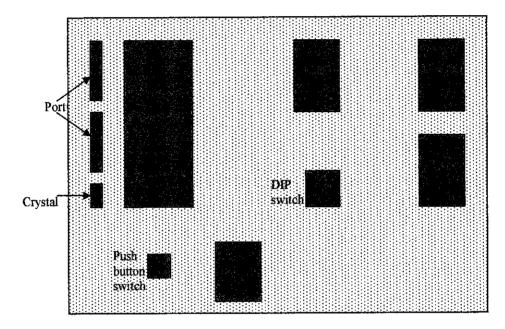


Figure 6 Microcontroller board layout

The Maze Mouse uses the 80C31 Intel microcontroller which belongs to the 8051 family. At this part of the mouse lays its brain that is fully responsible for its act.

There is basic [10]difference between a microcontroller and a CPU. With a microcontroller, the peripheral components like RAM, ROM, a serial port or an ADC or DAC are on chip. That means it is possible to realize complex system control functions with only one chip. For instance, we can use a microcontroller for the system control of a VTR or in a videotext decoder. Whatever that we intend to do with a microcontroller only depends on the software.

The 8051 was the first device that was available on the market. Designed by INTEL this chip already contains two 16 bit timer/counter, a serial port and an internal RAM. As an 87C51 the chip also contains the program memory on chip. The 80C31 is the ROMless version. Figure 7 shows a circuit diagram of an 80C31 with an external program memory.

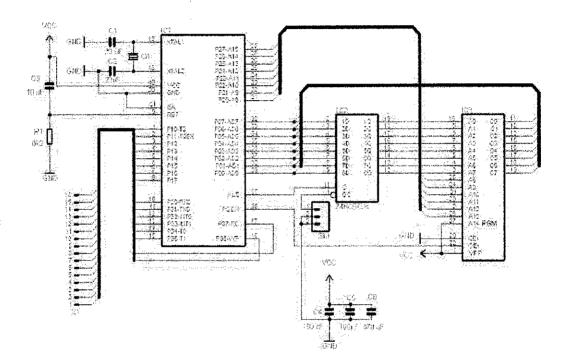


Figure 7 Circuit diagram of an 80C31 with an external program memory

Referring to the figure above, IC 1 is an 80C31. This chip contains four 8 bit ports (P0, P1, P2, and P3). In this example we are using an external memory. In that case Port 0 and 2 are used as an address/data bus. Pin 31 decides if we are to use this chip as a stand alone version or using an external program memory device. If we connect Pin 31 to ground, the 80C31 is forced to use the external memory instead of the internal one. EA stands for external access. In the first step, the microcontroller writes the address to the program memory. P0 contains the address low byte and P2 contains the address high byte. By using the ALE signal (Pin 30) the address low byte will be stored in IC2. ALE stands for address latch enable. In the second step, the microcontroller uses the PSEN signal to read the first command and it will be executed by the microcontroller. If the program is running, this procedure will

happen all the time. The clock signal will be generated by the crystal Q1, the internal circuit of the microcontroller and the capacitors C1 and C2. A typical value for the capacitors will be 33pF. The frequency of the crystal depends on the microcontroller device type. A typical value will be 12 -24 MHz. The reset signal will be generated by R1 and C3.

4.2 Infrared Sensor

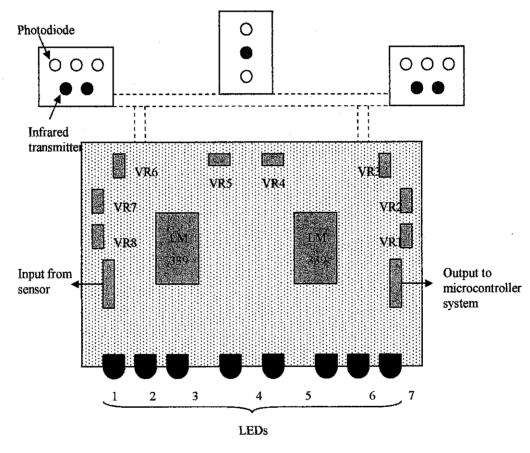


Figure below shows the layout of the sensor circuit board:

Figure 8 Infrared sensor circuit board

Referring to the above figure, the LED's will serve as the indicators to show which sensor is activated.

Figure below shows one particular infrared sensor circuit used by the maze mouse:

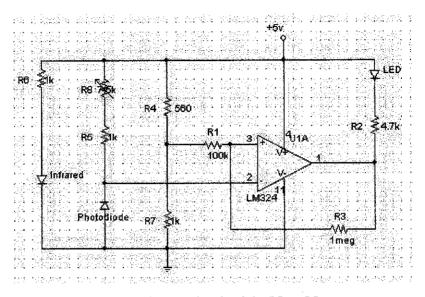


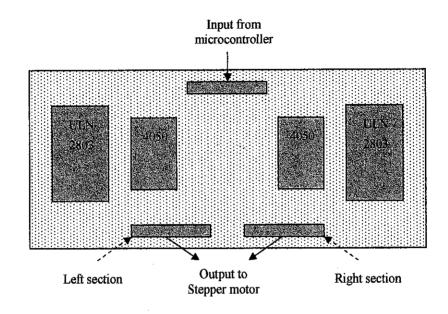
Figure 9 Sensor circuit of the Maze Mouse

Referring to the circuit above, the reference voltage is at the positive input of the comparator. The value of R6 depends on the number of sensor circuits to be combined. The complete schematic diagram in the appendix shows that 33Ω resistor is used for the combination of two circuits and 100Ω resistor is used for the combination of the circuits.

Basically, the infrared emitter produces an infrared beam which will be reflected by obstacles in front of it. This reflected signal should be detected by the photo diode. Upon detection, the respective LED's should light up. In other words, detection of infrared beam indicates the presence of obstacle and the microcontroller should react based on this input to direct the motors' movement.

In the Interim report I have produced last semester, the place of R7 in the circuit actually belongs to a 3.3V zener diode. However, it was changed to obtain a different reference voltage for the LM339 comparator. This is to improve on the sensor's performance.

4.3 Motor Driver



The layout for the motor driver circuit board is as shown below:

Figure 10 Motor driver circuit board layout

4.4 The Maze

The maze used in this project is a simple one. It will be built on a piece of wood (preferably plywood). The wood will be painted with two colours; black and white. The black paint represents walls and the white paint represents the path available. The white paint will reflect the infrared beam emitted by the infrared transmitter, and this reflected beam will reach the receiver. Therefore, detection of infrared beams indicates presence of a clear path.

In order for the mouse to navigate safely along the maze, the microcontroller is to be programmed with specific instructions based on the input from sensors. Up to this time, the following movements are to be followed by the mouse:

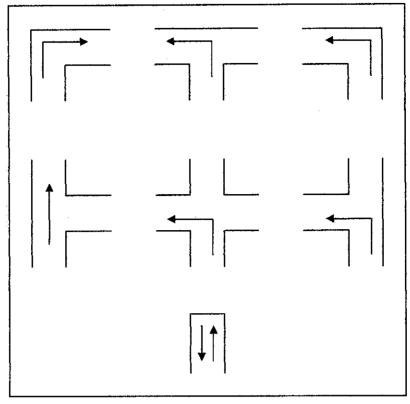


Figure 11 Movements of the mouse along the maze

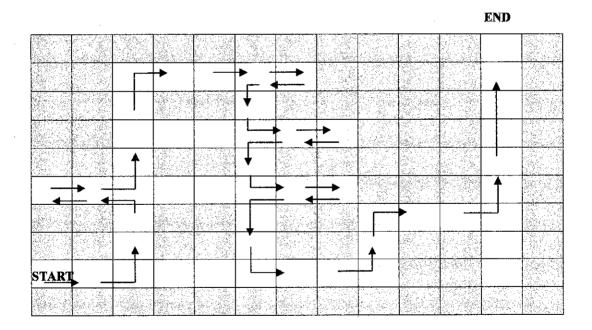


Figure 12 Example of a maze and the projected path of the mouse

4.5 Programming

To begin with the programming, we have first decided that detection of infrared beam by the receivers will be translated to logic 1 (high) and vice versa. In other words, high inputs from the sensors indicate existence of boundaries along the maze.

The table below shows the decision to be made by the microcontroller based on the inputs from the sensors:

Left Sensor	Forward sensor	Right sensor	Input to micro-c	Routing	Decision
Low	High	High	011	Left corner	Tum Left
High	High	Low	110	Right corner	Turn Right
High	Low	High	101	Straight line	Forward
Low	Low	Low	000	4 Junction	Turn Left
High	High	High	111	Dead End	Reverse
Low	Low	High	001	T Left Junction	Tum Left
High	Low	Low	100	T Right Junction	Forward
Low	High	Low	010	T Junction	Left

Table 4 Inputs from sensors and the corresponding actions

After the mouse has performed the respective action, the microcontroller will have to check that the mouse is moving in the forward direction. This will be done by checking that the inputs from the sensors equal to the value of 101. The whole operation can be described according to the following steps:

- 1. Inputs received from the sensors.
- 2. Inputs from sensors are compared with the stored bits in microcontroller register, one by one.

- 3. If input bits are equal to the stored bits, the microcontroller will make the corresponding decision, also in bits of three.
- 4. The decision bits will be sent to the motors, for them to make the right movement.
- 5. Microcontroller performs checking function for forward movement.

The steps above are summarized in the following flowchart:

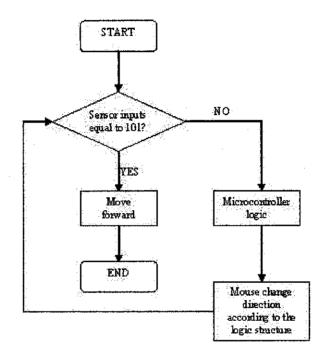


Figure 13 General flowchart of the mouse's operation

For the microcontroller program written, please refer to the appendix.

CHAPTER 5 CONCLUSION

As presented in this report, the project work has reached the objective, which is to develop a mouse that can find its own way out of a maze. The concept of a maze mouse is actually the basis of a mobile robot, which usage is getting more popular nowadays. The most important aspect is the ability of the mouse to detect obstacles awaiting it and to translate this information to determine its movement.

By integrating the microcontroller, the infra-red sensor and the motor driver components, we finally obtain a complete prototype of a maze mouse. The overall operation of the mouse is governed by a simple program written into the 80C31 microcontroller, together with the other supporting memory IC's. This particular program is the one responsible in translating the input coming from the sensors to the output, which is the motor movement. Lastly, for the mouse to be succeed in its operation, all its independent parts must first confirmed to be reliable and performing correctly as per requirement.

REFERENCES

[1] Reactive Navigation for Autonomous Guided Vehicle Using the Neuro-fuzzy Techniques; Jin Cao, Xiaoqun Liao, and Ernest Hall; Center for Robotics Research, ML 72; University of Cincinnati

[2] http://micromouse.cs.rhul.ac.uk/index.html

[3] http://reinerjansen.de/4flash/english version/hauptteil english version.html#basics

[4] http://www.fairchildsemi.com/an/AN/AN-3005.pdf

[5] http://www.fairchildsemi.com/products/opto/ir/prodnote.html#faq

[6] http://www.fairchildsemi.com/products/opto/ir/infrared.html

[7] http://home.cogeco.ca/~rpaisley4/ATDetIR.html

[8] http://www.netmotion.com/htm_files/adv_motors.htm#four

[9] http://reinerjansen.de/4flash/english version/hauptteil english version.html#basics

[10] http://reinerjansen.de/4flash/english_version/hauptteil_english_version.html#basics

APPENDIX A

Project Gantt Chart

GANTT CHART OF FIRST SEMESTER

ITEMS/WEEK	1	2	3. 3.	4	2	6	7 .	80	9.	10	11	12	13	14	15
Selection of project topic															
				-											
Preliminary research work															
Submission of Preliminary Report				♦											
Project work															
- Reference/Literature											-	-			
- Hardware construction															
- Maze construction															
				_											
Submission of Progress Report								•							
Project work continue										1. 1. 1. 1. 1. 1. 1. 1. 1. 1. 1. 1. 1. 1					
	- 12														
Submission of Interim Report final draft									-			•			
Submission of Interim Report														٠	
Oral presentation															٠

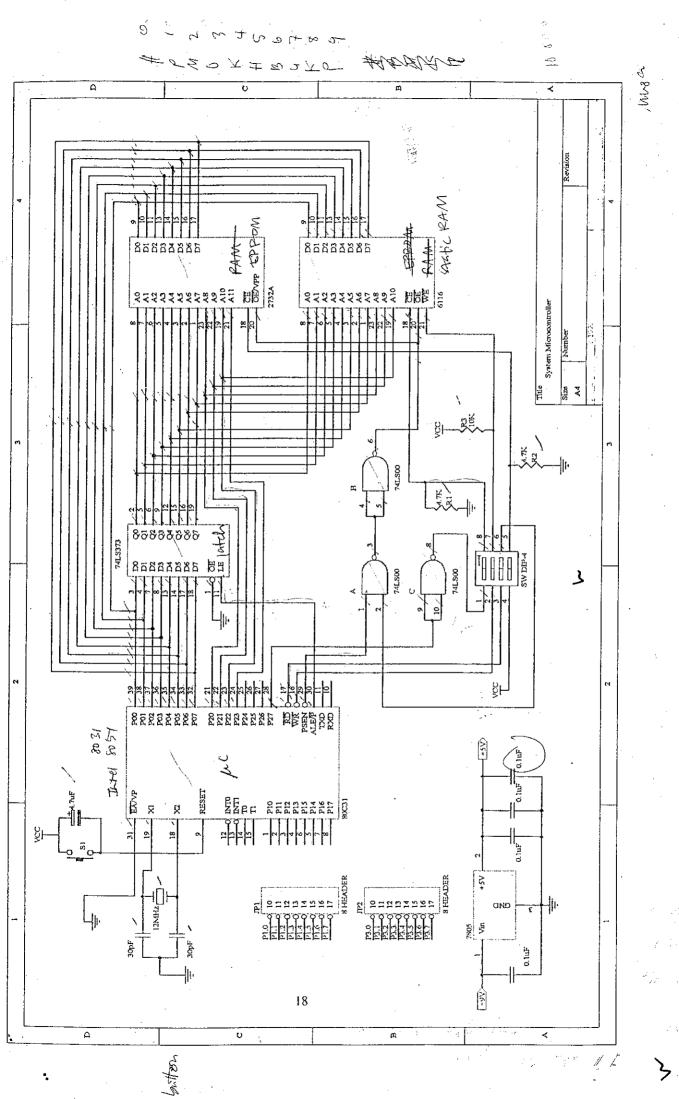
GANTT CHART OF SECOND SEMESTER

APPENDIX B

List of hardware used

List of hardware required for the Maze Mouse project:

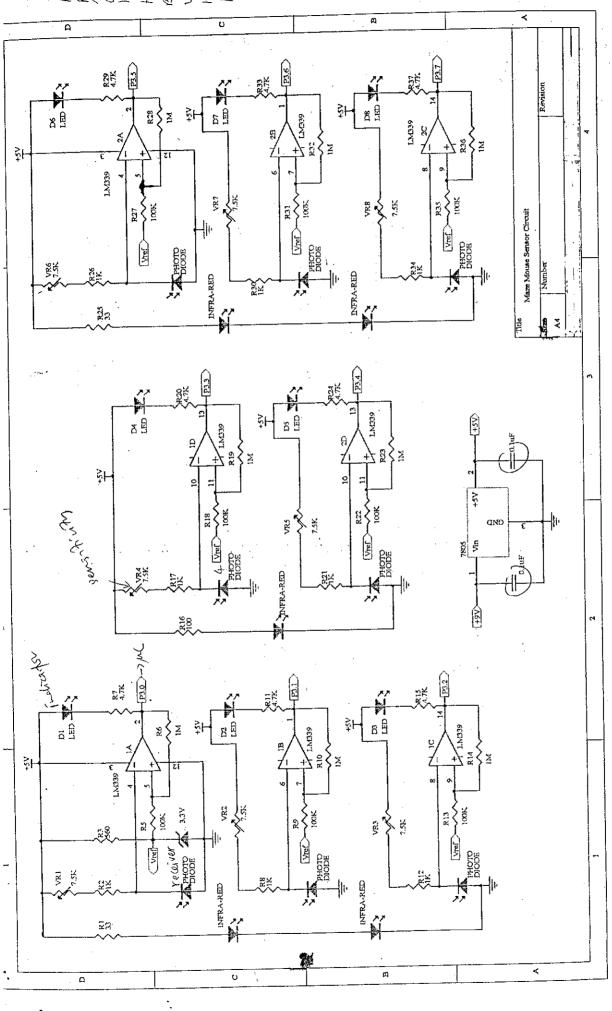
0.		ITEM	DESCRIPTION
1	IC:		
	1.	7805	Voltage regulator
	1	4050	Buffer
		ULN2803	Stepper motor driver
		80C31	Microcontroller
	5.	74LS373	Latch
	6.	74LS00	NAND gate
	7.	2732A	RAM
	8.	6116A	EPROM
	9.	LM339	Amplifier
2	Capaci	tor:	
	1.	100 μF	Electrolytic
		4.7 μF	Electrolytic
	3.	0.1 μF	
	4.	30 pF	
3	Resisto)r:	
	1.	4.7 kΩ	
	2.	10 kΩ	
	3.	560 Ω	
	4.	Variable resistor 10 k Ω	
4	Diode:		
	1.	1N4001	
	2.	Photo diode	
	3.	LED	
	4.	3.3V zener diode	
5	Others		
	1.	12MHz crystal oscillator	
	2.	5V stepper motor	
		8-pin header	
		Switch DIP-4	
	5.	Push button switch	
	1	Infrared sensor	
	7.	IC socket	
	1	Solder iron & solder lead	
		Vero board	
		Wire	
		Wire cutter	
		. Rainbow wire	

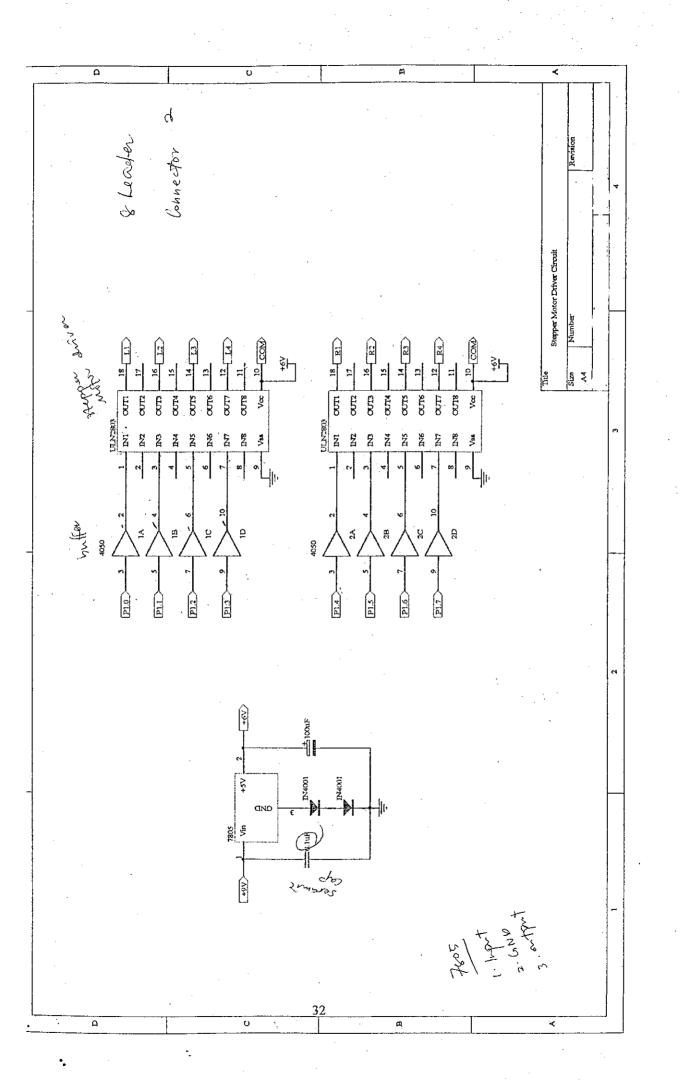


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APPENDIX D

Data sheets

INTEGRATED CIRCUITS

DATA SHEET

80C51/87C51/80C31 80C51 8-bit microcontroller family 4K/128 OTP/ROM/ROMless low voltage (2.7V–5.5V), low power, high speed (33 MHz)

Product specification Supersedes data of 1998 Oct 14 IC20 Data Handbook

1999 Apr 01

Philips Semiconductors





80C51 8-bit microcontroller family 4K/128 OTP/ROM/ROMiess, low voltage (2.7V–5.5V), low power, high speed (33 MHz)

Product specification

80C51/87C51/80C31

DESCRIPTION

The Philips 8XC51/31 is a high-performance static 80C51 design fabricated with Philips high-density CMOS technology with operation from 2.7V to 5.5V.

The 8XC51/31 contains a 4k \times 8 ROM, a 128 \times 8 RAM, 32 I/O lines, three 16-bit counter/timers, a six-source, four-priority level nested interrupt structure, a serial I/O port for either multi-processor communications, I/O expansion or full duplex UART, and on-chip oscillator and clock circuits.

In addition, the device is a low power static design which offers a wide range of operating frequencies down to zero. Two software selectable modes of power reduction—idle mode and power-down mode are available. The idle mode freezes the CPU while allowing the RAM, timers, serial port, and interrupt system to continue functioning. The power-down mode saves the RAM contents but freezes the oscillator, causing all other chip functions to be inoperative. Since the design is static, the clock can be stopped without loss of user data and then the execution resumed from the point the clock was stopped.

SELECTION TABLE

For applications requiring more ROM and RAM, see the 8XC52/54/58/80C32, 8XC51FA/FB/FC/80C51FA, and 8XC51RA+/RB+/RC+/80C51RA+ data sheet.

ROM/EPROM Memory Size (X by 8)	RAM Size (X by 8)	Programmable Timer Counter (PCA)	Hardware Watch Dog Timer
80C31/8XC51		· ·	
0K/4K	128	No	No
80C32/8XC52/54	/58		
0K/8K/16K/32K	256	No	No
80C51FA/8XC51	FA/FB/FC		
0K/8K/16K/32K	256	Yes	No
80C51RA+/8XC5	1RA+/RB+/RC	+	
0K/8K/16K/32K	512	Yes	Yes
8XC51RD+		· · · · · · · · · · · · · · · · · · ·	
64K	1024	Yes	Yes

FEATURES

- 8051 Central Processing Unit
 - 4k×8 ROM (80C51)
 - 128 × 8 RAM
 - Three 16-bit counter/timers
 - Full duplex serial channel
 - Boolean processor
 - Full static operation
 - Low voltage (2.7V to 5.5V@ 16MHz) operation
- Memory addressing capability
 - 64k ROM and 64k RAM
- Power control modes:
 - Clock can be stopped and resumed
 - Idle mode
 - Power-down mode
- CMOS and TTL compatible
- Three speed ranges at V_{CC} = 5V
 - 0 to 16MHz
 - 0 to 33MHz
- Three package styles
- Extended temperature ranges
- Dual Data Pointers
- Second DPTR register
- Security bits:
- ROM (2 bits)
- OTP/EPROM (3 bits)
- Encryption array—64 bytes
- 4 level priority interrupt
- 6 interrupt sources
- Four 8-bit I/O ports
- Full-duplex enhanced UART
 - Framing error detection
 - Automatic address recognition
- Programmable clock out
- Asynchronous port reset
- Low EMI (inhibit ALE)

2

Wake-up from Power Down by an external interrupt (8XC51)

80C51 8-bit microcontroller family 4K/128 OTP/ROM/ROMless, low voltage (2.7V–5.5V), low power, high speed (33 MHz)

80C51/87C51/80C31

Product specification

80C51/87C51 AND 80C31 ORDERING INFORMATION

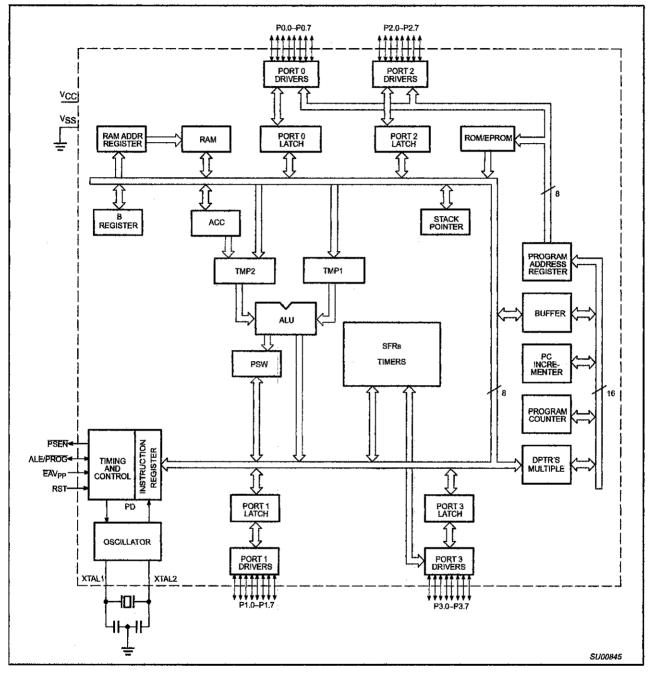
	MEMORY SIZE 4K × 8	ROMiess	TEMPERATURE RANGE °C AND PACKAGE	VOLTAGE RANGE	FREQ. (MHz)	DWG. #
ROM	P80C51SBPN	P80C31SBPN	0 to +70, Plastic Dual In-line Package	2.7V to 5.5V	0 to 16	SOT129-1
OTP	P87C51SBPN	FOUCATODEN		2.1 4 10 0.04	01010	301123-1
ROM	P80C51SBAA	P80C31SBAA	0 to +70. Plastic Leaded Chip Carrier	2.7V to 5.5V	0 to 16	SOT187-2
OTP	P87C51SBAA	FOUCSTODAA	0 to 170, Plastic Leaded Chip Carrier	2.7 0 10 0.0 0	0.010	0011072
ROM	P80C51SBBB	P80C31SBBB	0 to +70. Plastic Quad Flat Pack	2.7V to 5.5V	0 to 16	SOT307-2
OTP	P87C51SBBB	P80C313000		2.7 4 60 0.04	01010	0010012
RÓM	P80C51SFPN	P80C31SFPN	-40 to +85. Plastic Dual In-line Package	2.7V to 5.5V	0 to 16	SOT129-1
OTP	P87C51SFPN	POUCSIOFIN		2.7 4 10 0.04		0011201
ROM	P80C51SFA A	P80C31SFA A	-40 to +85, Plastic Leaded Chip Carrier	2.7V to 5.5V	0 to 16	SOT187-2
OTP	P87C51SFA A	FBOOSIGIAA		2.1 1 10 0.01		0011012
ROM	P80C51SFBB	P80C31SFBB	-40 to +85. Plastic Quad Flat Pack	2.7V to 5.5V	0 to 16	SOT307-2
OTP	P87C51SFBB	FOCSTOFEE		2.7 V 10 0.0 V		0010012
ROM	P80C51UBAA	P80C31UBAA	0 to +70, Plastic Leaded Chip Carrier	5V	0 to 33	SOT187-2
OTP	P87C51UBAA	1 DUCOTODAA	o to the Habita Leaded only carren			00.107 1
ROM	P80C51UBPN	P80C31UBPN	0 to +70, Plastic Dual In-line Package	5V	0 to 33	SOT129-1
ΟΤΡ	P87C51UBPN	POUCSTODEN	to to 170, maste buar mane i dokago		0.000	0011201
ROM	P80C51UBBB	P80C31UBBB	0 to +70, Plastic Quad Flat Pack	5V	0 to 33	SOT307-2
OTP	P87C51UBBB				01033	00.007.2
ROM	P80C51UFAA	P80C31UFAA	40 to +85, Plastic Leaded Chip Carrier	5V	0 to 33	SOT187-2
OTP	P87C51UFAA	POUCSTUFAA		54	010 00	001101-2
ROM	P80C51UFPN	P80C31UFPN	-40 to +85, Plastic Dual In-line Package	5V	0 to 33	SOT129-1
OTP	P87C51UFPN					0011201
ROM	P80C51UFBB	P80C31UFBB	-40 to +85, Plastic Quad Flat Pack	5V	0 to 33	SOT307-2
OTP	P87C51UFBB			J JV		00100.2

80C51/87C51 AND 80C31 ORDERING INFORMATION

DEVICE NUMBER (P87C51)	OPERATING FREQUENCY, MAX (S)	TEMPERATURE RANGE (B)	PACKAGE (AA)
P80C51 ROM	S = 16 MHz	B = 0° to +70°C	AA = PLCC
P87C51 OTP	U = 33 MHz	F = -40°C to +85°C	BB = PQFP
P80C31 ROMless			PN = PDIP

80C51/87C51/80C31

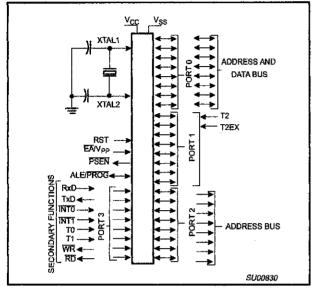
BLOCK DIAGRAM



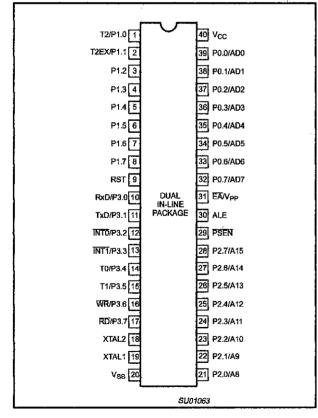
80C51 8-bit microcontroller family 4K/128 OTP/ROM/ROMless, low voltage (2.7V–5.5V), low power, high speed (33 MHz)

80C51/87C51/80C31

LOGIC SYMBOL



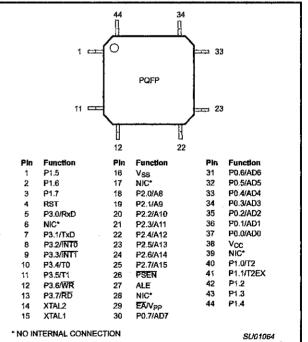
PIN CONFIGURATIONS



PLASTIC LEADED CHIP CARRIER PIN FUNCTIONS

		17				29	
		l	18		28		
Pin	Function		Pin	Function		Pin	Function
1	NIC*		16	P3.4/T0		31	P2.7/A15
2	P1.0/T2		17	P3.5/T1		32	PSEN
3	P1.1/T2EX		18	P3.6/WR		33	ALE
4	P1.2		19	P3.7/RD		34	NIC*
5	P1.3		20	XTAL2		35	EA/Vee
6	P1.4		21	XTAL1		36	P0.7/AD7
7	P1.5		22	Vss		37	P0.6/AD6
8	P1.6		23	NIC*		38	P0.5/AD5
9	P1,7		24	P2.0/A8		39	P0.4/AD4
10	RST		25	P2.1/A9		40	P0.3/AD3
11	P3.0/RxD		26	P2.2/A10		41	P0.2/AD2
12	NIC*		27	P2.3/A11		42	P0.1/AD1
13	P3.1/TxD		28	P2.4/A12		43	P0.0/AD0
14	P3.2/INT0		29	P2.5/A13		44	Vcc
15	P3.3/INTT		30	P2.6/A14			
* NO IN	TERNAL CO	NECTI	ON				SLI01062

PLASTIC QUAD FLAT PACK PIN FUNCTIONS



Order this document by ULN2803/D



Octal High Voltage, High Current Darlington Transistor Arrays

The eight NPN Darlington connected transistors in this family of arrays are ideally suited for interfacing between low logic level digital circuitry (such as TTL, CMOS or PMOS/NMOS) and the higher current/voltage requirements of lamps, relays, printer hammers or other similar loads for a broad range of computer, industrial, and consumer applications. All devices feature open-collector outputs and free wheeling clamp diodes for transient suppression.

The ULN2803 is designed to be compatible with standard TTL families while the ULN2804 is optimized for 6 to 15 volt high level CMOS or PMOS.

package, unless otherwise noted.)		-	,
Rating	Symbol	Value	Unit
Output Voltage	Vo	50	V
Input Voltage (Except ULN2801)	VI	30	v
Collector Current – Continuous	IC	500	mA
Base Current – Continuous	IВ	25	mA
Operating Ambient Temperature Range	ТА	0 to +70	°C
Storage Temperature Range	T _{stg}	-55 to +150	°C
Junction Temperature	Тj	125	°C

MAXIMUM RATINGS ($T_A = 25^{\circ}C$ and rating apply to any one device in the package, unless otherwise noted.)

R_{LUA} = 55°C/W

Do not exceed maximum current limit per driver.

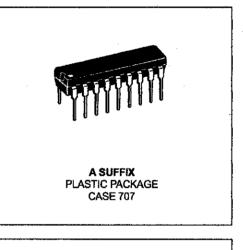
ORDERING INFORMATION

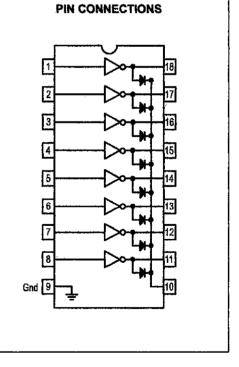
	(Characteristics	
Device	input Compatibility	V _{CE} (Max)/I _C (Max)	Operating Temperature Range
ULN2803A ULN2804A	TTL, 5.0 V CMOS 6 to 15 V CMOS, PMOS	50 V/500 mA	T _A = 0 to + 70°C

OCTAL PERIPHERAL DRIVER ARRAYS

ULN2803 ULN2804

SEMICONDUCTOR TECHNICAL DATA





© Motorola, Inc. 1996

ULN2803 ULN2804

ELECTRICAL CHARACTERISTICS (T_A = 25°C, unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit
Output Leakage Current (Figure 1) (V _O = 50 V, T _A = +70°C) (V _O = 50 V, T _A = +25°C)	All Types All Types	ICEX	_ _		100 50	DA
(V _O = 50 V, T _A = +70°C, V _I = 6.0 V) (V _O = 50 V, T _A = +70°C, V _I = 1.0 V)	ULN2802 ULN2804		-	-	500 500	
Collector-Emitter Saturation Voltage (Figure 2	2)	VCE(sat)	Ì			v
(IC = 350 mA, IB = 500 ⊡A)	All Types	(_	1.1	1.6	
(I _C = 200 mA, I _B = 350 ⊡A)	All Types	[- 1	0.95	1.3	ļ
(I _C = 100 mA, I _B = 250 □A)	All Types		-	0.85	1.1	
Input Current – On Condition (Figure 4)		li(on)				mA
$(V_1 = 17 V)$	ULN2802		-	0.82	1.25	1
$(V_1 = 3.85 V)$	ULN2803		-	0.93	1.35	
$(V_{\rm I} = 5.0 V)$	ULN2804		-	0.35	0.5	
$(V_{j} = 12 V)$	ULN2804		_	1.0	1.45	
Input Voltage – On Condition (Figure 5)		VI(on)				v
(V _{CE} = 2.0 V, I _C = 300 mA)	ULN2802		-	_	13	
$(V_{CE} = 2.0 \text{ V}, I_{C} = 200 \text{ mA})$	ULN2803		- 1	_	2.4	
$(V_{CE} = 2.0 V, I_C = 250 mA)$	ULN2803		- 1	-	2.7	
$(V_{CE} = 2.0 \text{ V}, I_{C} = 300 \text{ mA})$	ULN2803		ļ		3.0	ļ
$(V_{CE} = 2.0 \text{ V}, I_{C} = 125 \text{ mA})$	ULN2804		- 1	-	5.0	
$(V_{CE} = 2.0 \text{ V}, I_{C} = 200 \text{ mA})$	ULN2804		_	-	6.0	
(V _{CE} = 2.0 V, I _C = 275 mA)	ULN2804		- 1	-	7.0	
$(V_{CE} = 2.0 \text{ V}, I_{C} = 350 \text{ mA})$	ULN2804		-	-	8.0	
Input Current – Off Condition (Figure 3) (I _C = 500 \Box A, T _A = +70°C)	All Types	l(off)	50	100	-	DA
DC Current Gain (Figure 2) (V _{CE} = 2.0 V, I _C = 350 mA)	ULN2801	hFE	1000	_	_	_
Input Capacitance		Cl	. <u> </u>	15	25	pF
Tum-On Delay Time (50% El to 50% EO)	*****	ton		0.25	1.0	□s
Tum-Off Delay Time (50% El to 50% EO)		toff		0.25	1.0	۵s
Clamp Diode Leakage Current (Figure 6) (VR ≈ 50 V)	T _A = +25°C T _A = +70°C	^I R	_	-	50 100	DA
Clamp Diode Forward Voltage (Figure 7) (IF = 350 mA)		VF		1.5	2.0	V



www.fairchildsemi.com

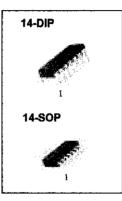
LM2901,LM339/LM339A,LM3302 LM239/LM239A Quad Comparator

Features

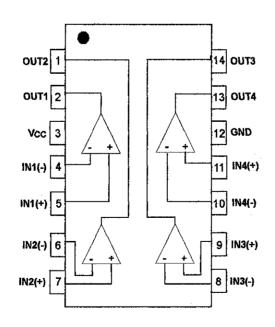
- Single or Dual Supply Operation
- Wide Range of Supply Voltage LM2901,LM339/LM339A,LM239/LM239A: 2 ~ 36V (or ±1 ~ ±18V)
- LM3302: $2 \sim 28V$ (or $\pm 1 \sim \pm 14V$)
- Low Supply Current Drain 800µA Typ.
- Open Collector Outputs for Wired and Connectors
- Low Input Bias Current 25nA Typ.
- Low Input Offset Current ±2.3nA Typ.
- Low Input Offset Voltage ±1.4mV Typ.
- Input Common Mode Voltage Range Includes Ground.
- Low Output Saturation Voltage
- Output Compatible With TTL, DTL and MOS Logic System

Description

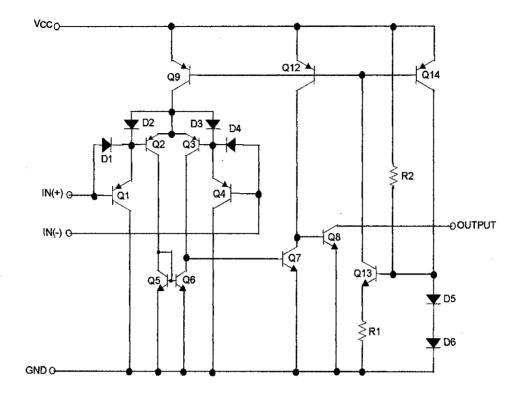
The LM2901, LM339/LM339A, LM239/LM239A, LM3302 consist of four independent voltage comparators designed to operate from single power supply over a wide voltage range.



Internal Block Diagram



Schematic Diagram



Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Supply Voltage	Vcc	±18 or 36	V
Supply Voltage only LM3302	Vcc	±14 or 28	V
Differential Input Voltage	VI(DIFF)	36	V
Differential Input Voltage Only LM3302	VI(DIFF)	28	V
Input Voltage	VI	-0.3 to +36	V
Input Voltage Only LM3302	VI	-0.3 to +28	V
Output Short Circuit to GND	-	Continuous	-
Power Dissipation	PD	570	mW
Operating Temperature LM339/LM339A LM2901/LM3302 LM239/LM239A	Topr	0 ~ +70 -40 ~ +85 -25 ~ +85	°C
Storage Temperature	TSTG	-65 ~ +150	°C

.

March 1998

FAIRCHILD

SEMICONDUCTOR M

DM74LS373/DM74LS374 3-STATE Octal D-Type Transparent Latches and Edge-Triggered Flip-Flops

General Description

These 8-bit registers feature totem-pole 3-STATE outputs designed specifically for driving highly-capacitive or relatively low-impedance loads. The high-impedance state and increased high-logic level drive provide these registers with the capability of being connected directly to and driving the bus lines in a bus-organized system without need for interface or pull-up components. They are particularly attractive for-implementing buffer registers, I/O ports, bidirectional bus drivers, and working registers.

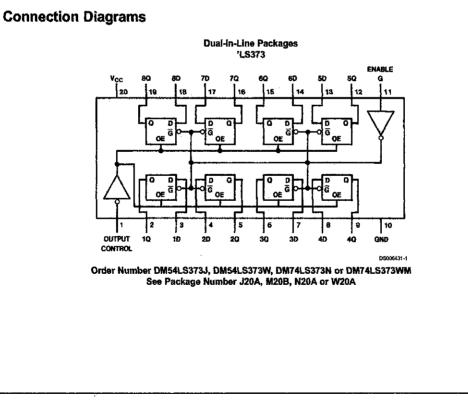
The eight latches of the DM54/74LS373 are transparent D-type latches meaning that while the enable (G) is high the Q outputs will follow the data (D) inputs. When the enable is taken low the output will be latched at the level of the data that was set up.

The eight flip-flops of the DM54/74LS374 are edge-triggered D-type flip flops. On the positive transition of the clock, the Q outputs will be set to the logic states that were set up at the D inputs.

A buffered output control input can be used to place the eight outputs in either a normal logic state (high or low logic levels) or a high-impedance state. In the high-impedance state the outputs neither load nor drive the bus lines significantly. The output control does not affect the internal operation of the latches or flip-flops. That is, the old data can be retained or new data can be entered even while the outputs are off.

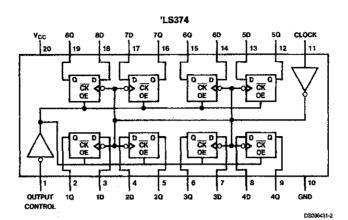
Features

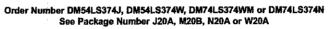
- Choice of 8 latches or 8 D-type flip-flops in a single package
- 3-STATE bus-driving outputs
- Full parallel-access for loading
- Buffered control inputs
- P-N-P inputs reduce D-C loading on data lines



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Connection Diagrams (Continued)





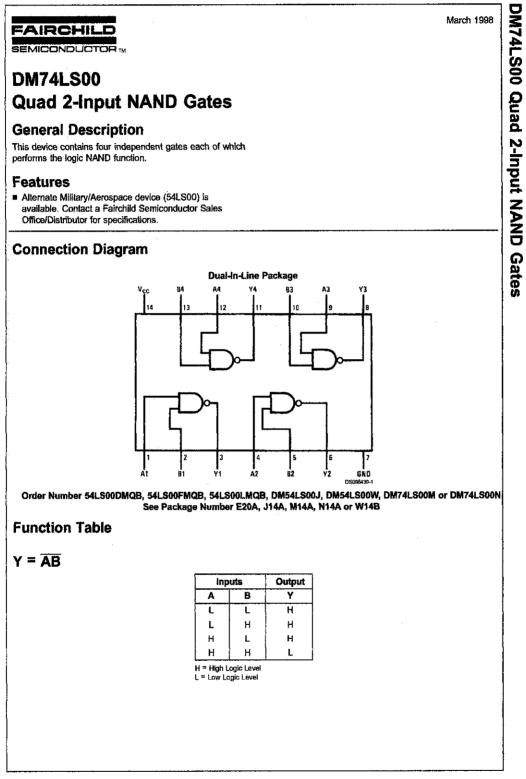
Function Tables DM54/74LS373

Output	Enable	D	Output
Control	G		
L	н	н	н
L	н	L	L
L	L	X	Qo
н	х	x	Z

H = High Level (Steedy State), L = Low Level (Steedy State), X = Don't Care \uparrow = Transition from low-to-high level, Z = High Impedance State Q_0 = The level of the output before steady-state input conditions were established.

DM54/74LS374

Output Control	Clock	D	Output
L	Î Î	Н	н
΄ L	↑	L	Ł
L	L L	x	Q ₀
н	X	X	Z



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Absolute Maximum Ratings (Note 1)

Supply Voltage	7V
Input Voltage	7V
Operating Free Air Temperature Range	

DM54LS and 54LS DM74LS Storage Temperature Range -55°C to +125°C 0"C to +70"C -65°C to +150°C

Recommended Operating Conditions

Symbol	Symbol Parameter		DM54LS00			DM74LS00			
			Nom	Max	Min	Nom	Max		
V _{cc}	Supply Voltage	4.5	5	5.5	4.75	5	5.25	V	
V _{BH}	High Level Input Voltage	2			2			V	
VIL	Low Level Input Voltage		· · · ·	0.7		1	0.8	V	
l _{on}	High Level Output Current			-0.4			-0.4	Mm	
OL	Low Level Output Current			4			8	mA	
TA	Free Air Operating Temperature	-55		125	0	1	70	°C	

Note 1: The "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. The device should not be operated at these limits. The parametric values defined in the "Electional Characteristics" table are not guaranteed at the absolute maximum ratings. The "Recommended Operating Conditions" table will define the conditions for actual device operation.

Electrical Characteristics

over recommended operating free air temperature range (unless otherwise noted)

Symbol	Parameter	Conditions		Min	Typ (Note 2)	Max	Units
V _i	Input Clamp Voltage	V _{cc} = Min, I _l = -18 mA				-1.5	v
VoH	High Level Output	V _{cc} = Min, I _{oH} = Max,	DM54	2.5	3.4		V
	Voltage	V _{iL} = Max	DM74	2.7	3.4		
VoL	Low Level Output	V _{CC} = Min, I _{OL} = Max,	DM54	[0.25	0.4	
	Voltage	V _{IH} ≂ Min	DM74		0.35	0.5	v
		I _{OL} = 4 mA, V _{CC} = Min	DM74		0.25	0.4	
կ	Input Current @ Max	V _{CC} = Max, V _I = 7V				0.1	mA
	Input Voltage						
l _{IH}	High Level Input Current	V _{CC} = Max, V _I = 2.7V				20	μA
l _{IL}	Low Level Input Current	V _{CC} = Max, V ₁ = 0.4V				-0.36	mА
los	Short Circuit	V _{cc} = Max	DM54	-20		-100	mA
	Output Current	(Note 3)	DM74	-20		-100	
I _{CCH}	Supply Current with	V _{cc} = Max			0.8	1.6	mA
	Outputs High					ł	
I _{CCL}	Supply Current with	V _{cc} ≖ Max	· · · · · ·		2.4	4.4	mA
	Outputs Low						

Switching Characteristics at V_{CC} = 5V and T_A = 25°C

		$R_{L} = 2 k\Omega$				
Symbol	Parameter	C _L =	15 pF	C_ =	50 pF	Units
		Min	Max	Min	Max	1
t _{PLH}	Propagation Delay Time	-3	10	4	15	лs
	Low to High Level Output	1				}
t _{PHL}	Propagation Delay Time	3	10	4	15	ns
	High to Low Level Output					

Note 2: All typicals are at V_{CC} = 5V, T_A = 25°C.

Note 3: Not more than one output should be shorted at a time, and the duration should not exceed one second.

FAIRCHILD

SEMICONDUCTOR

CD4049UBC • CD4050BC Hex Inverting Buffer • **Hex Non-Inverting Buffer**

General Description

The CD4049UBC and CD4050BC hex buffers are monolithic complementary MOS (CMOS) integrated circuits constructed with N- and P-channel enhancement mode transistors. These devices feature logic level conversion using only one supply voltage (V_{DD}). The input signal high level (V_{IH}) can exceed the V_{DD} supply voltage when these devices are used for logic level conversions. These devices are intended for use as hex buffers, CMOS to DTL/ TTL converters, or as CMOS current drivers, and at V_{DD} = 5.0V, they can drive directly two DTL/TTL loads over the full operating temperature range.

Features

- Wide supply voltage range: 3.0V to 15V
- Direct drive to 2 TTL loads at 5.0V over full temperature range

October 1987

Revised April 2002

- High source and sink current capability
- Special input protection permits input voltages greater than V_{DD}

Applications

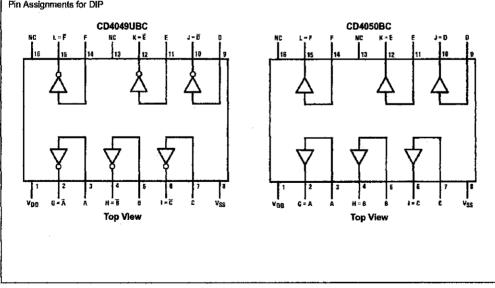
- · CMOS hex inverter/buffer
- · CMOS to DTL/TTL hex converter
- · CMOS current "sink" or "source" driver
- CMOS HIGH-to-LOW logic level converter

Ordering Code:

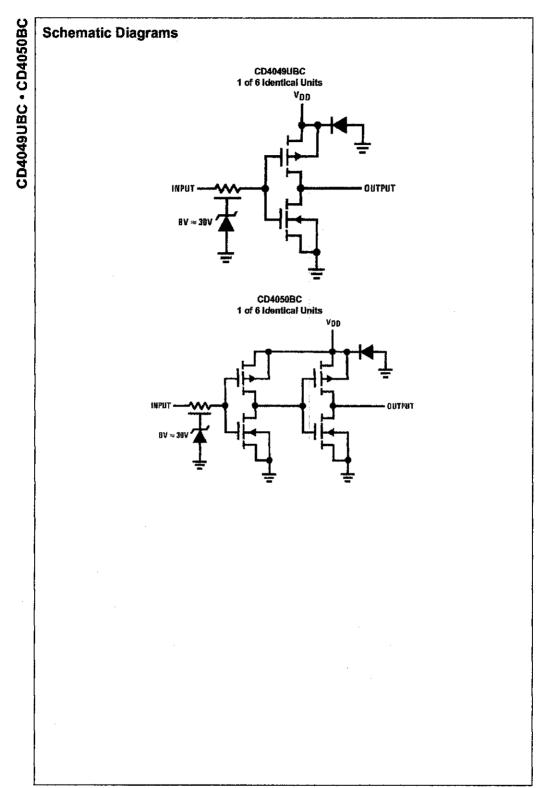
Order Number	Package Number	Package Description
CD4049UBCM	M16A	16-Lead Small Outline Integrated Circuit (SOIC), JEDEC MS-012, 0.150" Narrow
CD4049UBCN	N16E	16-Lead Plastic Dual-In-Line Package (PDIP), JEDEC MS-001, 0.300" Wide
CD4050BCM	M16A	16-Lead Small Outline Integrated Circuit (SOIC), JEDEC MS-012, 0.150" Narrow
CD4050BCN	N16E	16-Lead Plastic Dual-In-Line Package (PDIP), JEDEC MS-001, 0.300" Wide
Devices also available	in Tage and Reel, Specify	/ by appending the suffix letter "X" to the ordering code.

Connection Diagrams

Pin Assignments for DIP



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2

Absolute Maximum Ratings(Note 1) (Note 2)

Recommended Operating Conditions (Note 2)

• •	
Supply Voltage (V _{DD})	-0.5V to +18V
Input Voltage (V _{IN})	-0.5V to +18V
Voltage at Any Output Pin (V _{OUT})	0.5V to V _{DD} + 0.5V
Storage Temperature Range (T _S)	–65°C to +150°C
Power Dissipation (PD)	· · · ·
Dua-In-Line	700 mW
Small Outline	500 mW
Lead Temperature (TL)	
(Soldering, 10 seconds)	260°C

Supply Voltage (V _{DD})	3V to 15V
Input Voltage (V _{IN})	0V to 15V
Voltage at Any Output Pin (VOUT)	0 to V _{DD}
Operating Temperature Range (TA)	
CD4049UBC, CD4050BC	55°C to +125°C
Note 1: "Absolute Maximum Ratings" are those v	alues beyond which the

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed; they are not meant to imply that the devices should be operated at these limits. The table of "Recommended Operating Conditions" and "Electrical Characteristics" provides conditions for actual device operation. Note 2: $V_{SS} \approx 0V$ unless otherwise specified.

DC Electrical Characteristics (Note 3)

Symbol	Parameter	Conditions	-5	5°C		+25°C		+12	5°C	Units
зушрог	- Fatswebst	Conditions	Min	Max	Min	Тур	Max	Min	Max	Unita
DD	Quiescent Device Current	V _{DD} = 5V		1.0		0.01	1.0		30	
		V _{DD} = 10V		2.0		0.01	2.0		60	μA
		V _{DD} == 15V		4.0		0.03	4.0		120	
VOL	LOW Level Output Voltage	$V_{lH} = V_{DD}, V_{lL} = 0V,$								
		lo < 1 μA								
		V _{DD} = 5V		0.05		-0	0.05		0.05	
		V _{DD} = 10V		0.05		.0	0.05		0.05	۷
		V _{DD} ⇔ 15V		0.05		0	0.05		0.05	
VOH	HIGH Level Output Voltage	$V_{iH} = V_{DD}, V_{iL} = 0V,$			1					
		l ₀] < 1 μΑ		1						
		V _{DD} = 5V	4.95		4.95	-5		4.95		
		V _{DD} = 10V	9.95		9.95	10		9.95		V
		V _{DD} = 15V	14.95		14.95	15		14.95		
V _{aL}	LOW Level Input Voltage	loi < 1 μA				-				
	(CD4050BC Only)	$V_{DD} = 5V, V_{O} = 0.5V$		1.5	:	2.25	1.5		1.5	
		V _{DD} = 10V, V _O = 1V		3.0		4.5	3.0		3,0	v
		$V_{DD} = 15V, V_0 = 1.5V$		4.0		6.75	4.0		4.0	
VIL	LOW Level Input Voltage]lo < 1 µA								
	(CD4049UBC Only)	$V_{DD} = 5V, V_0 = 4.5V$		1.0		1.5	1.0		1.0	
		V _{DD} = 10V, V _O = 9V		2.0		2.5	2.0		2.0	v
		V _{DD} = 15V, V _O = 13.5V		3.0	1	3.5	3.0] '	3.0	
VIH	HIGH Level Input Voltage	lo < 1 μA								
	(CD4050BC Only)	V _{OD} = 5V, V _O = 4.5V	3.5		3,5	2.75		3.5		
		V _{DD} = 10V, V _O = 9V	7.0		7.0	5.5		7.0		v
		V _{DD} = 15V, V _O = 13.5V	11.0		11.0	8.25		11.0		
ViH	HIGH Level Input Voltage	lo < 1 μA								
	(CD4049UBC Only)	V _{DD} = 5V, V _O = 0.5V	4.0		4.0	3.5		4.0		
		$V_{DD} = 10V, V_{O} = 1V$	8.0	i i	8.0	7.5		8.0		v
		$V_{DD} = 15V, V_{O} = 1.5V$	12.0		12.0	11.5]	12.0		
IOL	LOW Level Output Current	$V_{IH} = V_{DD}, V_{IL} = 0V$	-		:					
	(Note 4)	$V_{DD} = 5V, V_{O} = 0.4V$	5.6		4.6	5		3.2		
		$V_{DD} = 10V, V_{O} = 0.5V$	12		9.8	12		6.8		mA
		V _{DD} = 15V, V _O = 1.5V	35		29	40		20		
IOH	HIGH Level Output Current	$V_{1H} = V_{DD}, V_{1L} = 0V$		[1
	(Note 4)	$V_{DD} = 5V, V_{D} = 4.6V$	-1.3		-1.1	1.6	ľ	0.72		
		V _{DD} = 10V, V _O = 9.5V	2.6		-2.2	3.6	-	-1.5		mA
		V _{DD} = 15V, V _O = 13.5V	-8.0		-7.2	-12		-5		1
l _{in}	Input Current	V _{DD} = 15V, V _{IN} = 0V		-0.1	1	-10-5	-0.1	[-1.0	μА
		V _{DD} = 15V, V _{IN} = 15V		0.1		10-5	0.1	1	1.0	μM

3

DC Electrical Characteristics (Continued) Note 4: These are peak output current capabilities. Continuous output current is rated at 12 mA maximum. The output current should not be allowed to exceed this value for extended periods of time. I_{OL} and i_{OH} are tested one output at a time.

AC Electrical Characteristics (Note 5) CD4049UBC

		Conditions	Min	Тур	Max	Units
HL	Propagation Delay Time	V _{DD} ⇒5V		30	65	
	HIGH-to-LOW Level	$V_{DD} = 10V$		20	40	ns
		V _{DD} = 15V		15	30	
LH	Propagation Delay Time	$V_{DD} = 5V$		45	85	
	LOW-to-HIGH Level	V _{DD} = 10V		25	45	ns
		V _{DD} = 15V		20	35	
	Transition Time	V _{DD} = 5V		30	60	
	HIGH-to-LOW Level	V _{DD} = 10V		20	40	ns
		V _{DD} ≠ 15V		15	30	
LH	Transition Time	V _{DD} = 5V		60	120	
	LOW-to-HIGH Level	$V_{0D} = 10V$		30	55	ns
		V _{DD} = 15V		25	45	
IN	Input Capacitance	Any input		15	22.5	pF
	ameters are guaranteed by DC corrections are guaranteed by DC corrections of the second secon	stics (Note 6)	ified			. <u></u>
	trical Characteri	-	ified Min		Max	Units
AC Elec CD4050BC T _A = 25°C, C Symbol	trical Characteri $t_L = 50 \text{ pF}, \text{R}_L = 200 \text{k}, t_r = t_r = 100 \text{ k}$	StiCS (Note 6) = 20 ns, unless otherwise spec		Тур 60	Max 110	L <u></u>
AC Elec CD4050BC T _A = 25°C, C Symbol	trical Characteri	stics (Note 6) = 20 ns, unless otherwise spec		Тур		L <u></u>
AC Elec CD4050BC T _A = 25°C, C Symbol	trical Characteri	Stics (Note 6) = 20 ns, unless otherwise spec Conditions V_DD = 5V		Τyρ 60	110	Units
AC Elec CD4050BC T _A = 25°C, C Symbol ¹ HL	trical Characteri	Stics (Note 6) = 20 ns, unless otherwise spectrum Conditions V _{DD} = 5V V _{DD} = 10V		Тур 60 25	110 55	Units
AC Elec CD4050BC T _A = 25°C, C Symbol ¹ HL	trical Characteri	Stics (Note 6) = 20 ns, unless otherwise spectrum Conditions V _{DD} = 5V V _{DD} = 10V V _{DD} = 15V V _{DD} = 15V		Тур 60 25 20	110 55 30	Units
AC Elec CD4050BC T _A = 25°C, C Symbol ¹ HL	Etrical Characteri t_ = 50 pF, R_L = 200k, t, = t _f = Propagation Delay Time HIGH-to-LOW Level Propagation Delay Time	Stics (Note 6) = 20 ns, unless otherwise spectrum Vpn = 5V Vpn = 10V Vpn = 15V Vpn = 5V Vpn = 5V		Тур 60 25 20 60	110 55 30 120	Units
AC Elec CD4050BC T _A = 25°C, C Symbol PHL	Etrical Characteri t_ = 50 pF, R_L = 200k, t, = t _f = Propagation Delay Time HIGH-to-LOW Level Propagation Delay Time	Stics (Note 6) = 20 ns, unless otherwise spect Conditions V _{DD} = 5V V _{DD} = 10V V _{DD} = 15V V _{DD} = 5V V _{DD} = 5V V _{DD} = 10V V _{DD} = 15V V _{DD} = 15V V _{DD} = 15V V _{DD} = 15V		Тур 60 25 20 60 30	110 55 30 120 55	Units
AC Elec CD4050BC T _A = 25°C, C Symbol ¹ HL	Propagation Delay Time HIGH-to-LOW Level	Stics (Note 6) = 20 ns, unless otherwise spect Conditions V _{DD} = 5V V _{DD} = 10V V _{DD} = 15V V _{DD} = 5V V _{DD} = 5V V _{DD} = 5V V _{DD} = 5V V _{DD} = 10V		Тур 60 25 20 60 30 25	110 55 30 120 55 45	Units
AC Elec CD4050BC T _A = 25°C, C Symbol HL	Propagation Delay Time HIGH-to-LOW Level Propagation Delay Time HIGH-to-LOW Level Propagation Delay Time LOW-to-HIGH Level Transition Time	Stics (Note 6) = 20 ns, unless otherwise spect Conditions V _{DD} = 5V V _{DD} = 10V V _{DD} = 15V V _{DD} = 5V V _{DD} = 5V V _{DD} = 15V V _{DD} = 15V V _{DD} = 15V V _{DD} = 15V V _{DD} = 5V V _{DD} = 5V V _{DD} = 5V		Тур 60 25 20 60 30 25 30	110 55 30 120 55 45 60	ns
AC Elec CD4050BC T _A = 25°C, C Symbol PHL	Propagation Delay Time HIGH-to-LOW Level Propagation Delay Time HIGH-to-LOW Level Propagation Delay Time LOW-to-HIGH Level Transition Time	Stics (Note 6) = 20 ns, unless otherwise spect Conditions V _{DD} = 5V V _{DD} = 10V V _{DD} = 15V V _{DD} = 15V V _{DD} = 5V V _{DD} = 10V V _{DD} = 5V V _{DD} = 10V V _{DD} = 10V V _{DD} = 10V V _{DD} = 10V V _{DD} = 10V		Тур 60 25 20 60 30 25 30 20	110 55 30 120 55 45 60 40	ns
AC Elec CD4050BC T _A = 25°С, С Symbol ⁷ HL ¹ LH	Propagation Delay Time HIGH-to-LOW Level Transition Time HIGH-to-LOW Level	Stics (Note 6) = 20 ns, unless otherwise spect Conditions V _{DD} = 5V V _{DD} = 10V V _{DD} = 15V V _{DD} = 5V V _{DD} = 5V V _{DD} = 15V V _{DD} = 5V V _{DD} = 10V V _{DD} = 10V V _{DD} = 15V V _{DD} = 5V V _{DD} = 10V V _{DD} = 15V V _{DD} = 15V		Тур 60 25 20 60 30 25 30 20 15	110 56 30 120 55 45 60 40 30	ns
AC Elec CD4050BC T _A = 25°C, C Symbol HL HL	Propagation Delay Time HIGH-to-LOW Level Propagation Delay Time HIGH-to-LOW Level Transition Time HIGH-to-LOW Level	Stics (Note 6) = 20 ns, unless otherwise spect Conditions V _{DD} = 5V V _{DD} = 10V V _{DD} = 15V V _{DD} = 15V V _{DD} = 5V V _{DD} = 10V V _{DD} = 15V V _{DD} = 10V V _{DD} = 15V V _{DD} = 15V V _{DD} = 5V V _{DD} = 5V V _{DD} = 5V V _{DD} = 5V V _{DD} = 5V V _{DD} = 5V		Тур 60 25 20 60 30 25 30 20 15 60	110 56 30 120 55 45 60 40 30 120	ns ns



CMOS Static RAM 16K (2K x 8-Bit)

Features

- High-speed access and chip select times
- Military: 20/25/35/45/55/70/90/120/150ns (max.)
- Industrial: 20/25/35/45ns (max.)
- Commercial: 15/20/25/35/45ns (max.)
- Low-power consumption
- Battery backup operation
 - 2V data retention voltage (LA version only)
- Produced with advanced CMOS high-performance technology
- CMOS process virtually eliminates alpha particle soft-error rates
- Input and output directly TTL-compatible
- Static operation: no clocks or refresh required
- Available in ceramic and plastic 24-pin DIP, 24-pin Thin Dip, 24-pin SOIC and 24-pin SOJ
- Military product compliant to MIL-STD-833, Class B

Description

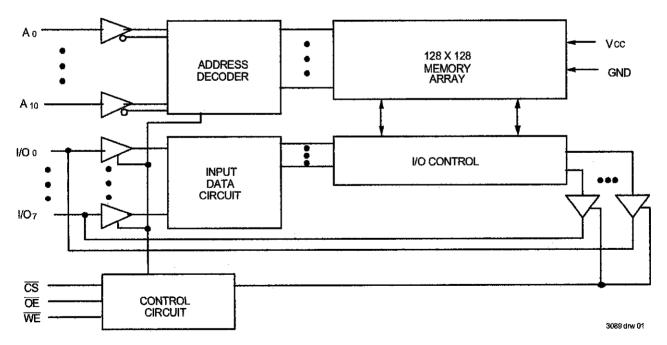
The IDT6116SA/LA is a 16,384-bit high-speed static RAM organized as 2K x 8. It is fabricated using IDT's high-performance, high-reliabilityCMOS technology.

Access times as fast as 15ns are available. The circuit also offers a reduced power standby mode. When \overline{CS} goes HIGH, the circuit will automatically go to, and remain in, a standby power mode, as long as \overline{CS} remains HIGH. This capability provides significant system level power and cooling savings. The low-power (LA) version also offers a battery backup data retention capability where the circuit typically consumes only 1 μ W to 4 μ W operating off a 2V battery.

All inputs and outputs of the IDT6116SA/LA are TTL-compatible. Fully static asynchronous circuitry is used, requiring no clocks or refreshing for operation.

The IDT6116SA/LA is packaged in 24-pin 600 and 300 mil plastic or ceramic DIP, 24-lead gull-wing SOIC, and 24-lead J-bend SOJ providing high board-level packing densities.

Military grade product is manufactured in compliance to the latest version of MIL-STD-883, Class B, making it ideally suited to military temperature applications demanding the highest level of performance and reliability.



Functional Block Diagram

FEBRUARY 2001

IDT6116SA/LA

CMOS Static RAM 2K (16K x 8-Bit)

Pin Configurations

$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	P24-2 P24-1 D24-2 D24-1 SO24-2 SO24-4	24 VCC 23 A8 22 A9 21 WE 20 OE 19 A10 18 CS 17 VO7 16 VO7 16 VO6 15 V/05 14 V/04 13 V/03
---	--	--

3089 drw 02

DIP/SOIC/SOJ Top View

Pin Description

Name	Description
Ao - A1o	Address Inputs
1/Qo - 1/O7	Data input/Output
CS	Chip Select
WE	Write Enable
ŌE	Output Enable
Vcc	Power
GND	Ground

3089 1bi 01

Truth Table⁽¹⁾

Mode	CS	OE WE		1/0	
Standby	H	X	Х	High-Z	
Read	L	Ĺ	Н	DATAout	
Read	L	Н	H	High-Z	
Write	L	X	L	DATAN	

3689 tbl 02

Military, Commercial, and Industrial Temperature Ranges

Capacitance (TA = +25°C, f = 1.0 MHz)

Symbol	Parameter ⁽¹⁾	Conditions	Max.	Unit
Cin	Input Capacitance	Vin = OV	- 8 -	pF
Civo	VO Capacitance	Vout = 0 V	8	pF
				3089 tht 03

NOTE:

1. This parameter is determined by device characterization, but is not production tested.

Absolute Maximum Ratings⁽¹⁾

Symbol	Rating	Com ^r l.	Mil.	Unit
Vterm ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to +7.0	-0.5 to +7.0	۷
Ta	Operating Temperature	0 to +70	-55 to +125	°C
Tbias	Temperature Under Bias	-55 to +125	-65 to +135	°C
Tsig	Storage Temperature	-55 to +125	-65 to +150	°C
PT	Power Dissipation	1.0	1.0	W
юлт	DC Output Current	50	50	mA
watre.			l I	3069 661 04

NOTES:

 Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

2. VTERM must not exceed Vcc +0.5V.

NOTE:

1. H = ViH, L = ViL, X = Don't Care.



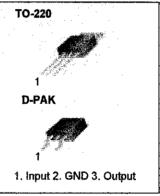
MC78XX/LM78XX/MC78XXA 3-Terminal 1A Positive Voltage Regulator

Features

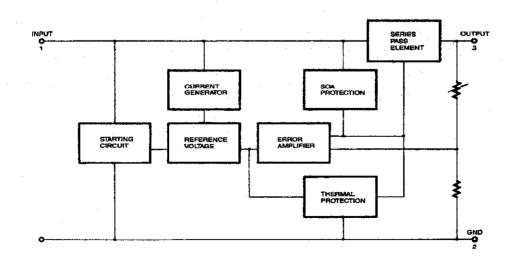
- Output Current up to 1A
- Output Voltages of 5, 6, 8, 9, 10, 12, 15, 18, 24V
- Thermal Overload Protection
- Short Circuit Protection
- Output Transistor Safe Operating Area Protection

Description

The MC78XX/LM78XX/MC78XXA series of three terminal positive regulators are available in the TO-220/D-PAK package and with several fixed output voltages, making them useful in a wide range of applications. Each type employs internal current limiting, thermal shut down and safe operating area protection, making it essentially indestructible. If adequate heat sinking is provided, they can deliver over 1A output current. Although designed primarily as fixed voltage regulators, these devices can be used with external components to obtain adjustable voltages and currents.







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Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Input Voltage (for V _O = 5V to 18V) (for V _O = 24V)	Vi Vi	35 40	V V
Thermal Resistance Junction-Cases (TO-220)	Rejc	5	°C/W
Thermal Resistance Junction-Air (TO-220)	Reja	65	°C/W
Operating Temperature Range	TOPR	0 ~ +125	°C
Storage Temperature Range	TSTG	-65 ~ +150	°C

Electrical Characteristics (MC7805/LM7805)

(Refer to test circuit ,0°C < TJ < 125°C, IO = 500mA, VI = 10V, CI= 0.33µF, CO= 0.1µF, unless otherwise specified)

Parameter	O. mahal	Symbol Conditions		MC7805/LM7805			11-14
Parameter	Symbol			Min.	Тур.	Max.	Unit
	·	TJ =+25 °C		4.8	5.0	5.2	
Output Voltage	Vo	5.0mA \leq lo \leq 1.0A, Po \leq 15W VI = 7V to 20V		4.75	5.0	5.25	v
(ina Pagulation (Notof)	Regline	Tj=+25 ℃	Vo = 7V to 25V	-	4.0	100	mV
Line Regulation (Note1)			VI = 8V to 12V	-	1.6	50	
			Io = 5.0mA to1.5A	-	9	100	mV
Load Regulation (Note1)	Regload TJ=+25	TJ=+25 ⁰C	lo =250mA to 750mA	- '	4	50	
Quiescent Current	lq	TJ =+25 °C	TJ =+25 °C		5.0	8.0	mA
- · · · · · · · ·	Δία	IO = 5mA to 1.	.0A	-	0.03	0.5	
Quiescent Current Change		VI= 7V to 25V		-	0.3	1.3	mA
Output Voltage Drift	ΔVο/ΔΤ	lo= 5mA		-	-0.8	-	mV/ °C
Output Noise Voltage	VN	f = 10Hz to 100KHz, TA=+25 °C		-	42	-	μV/Vo
Ripple Rejection	RR	f = 120Hz Vo = 8V to 18V		62	73	-	dB
Dropout Voltage	VDrop	IO = 1A, TJ =+25 °C		-	2	-	V
Output Resistance	ro	f = 1KHz		-	15	-	mΩ
Short Circuit Current	isc	VI = 35V, TA =+25 °C		-	230	-	mA
Peak Current	IPK	Tj =+25 °C			2.2	-	A

Note:

1. Load and line regulation are specified at constant junction temperature. Changes in Vo due to heating effects must be taken into account separately. Pulse testing with low duty is used.

APPENDIX E

Microcontroller program

32

main:

mov A, p1 ;read sensor status from p1 - load to accumulator mov p2, #01h mov p3, #01h ljmp condition

condition:

cjne A, #00h, condition1 ; check for 4 junction ljmp status

status:

mov p2, #01h ; mouse turn left mov p3, #08h mov A, p1 ; read current input from p1 cjne A, #05h, main ljmp status

condition1:

cjne A, #01h, condition2 ; check 4 T left corner ljmp status1

status1

mov p2, #01h; mouse turn left mov p3, #08h mov A, p1; read current input from p1 cjne A, #05h, main ljmp status1

condition2:

cjne A, #02h, condition3 ; check 4 T junction ljmp status2

status2

mov p2, #01h; mouse turn left mov p3, #08h mov A, p1; read current input from p1 cjne A, #05h, main ljmp status2

condition3:

cjne A, #03h, condition4 : check 4 left corner ljmp status3

status3

mov p2, #01h ; mouse turn left mov p3, #08h mov A, p1 ; read current input from p1 cjne A, #05h, main ljmp status3

condition4:

cjne A, #04h, condition5 ; check 4 T right junction lmjp status4

status4:

mov p2, #08h; mouse turn right mov p3, #01h mov A, p1; read current input from p1 cjne A, #05h, main ljmp status4

condition5:

cjne A, #05h, condition6 ; check 4 straight line lmjp status5

status5:

mov p2, #01h; port 2 to right motor mov p3, #01h; port 3 to left motor mov A, p1; read current input from p1 cjne A, #05h, main ljmp status5

condition6:

cjne A, #06h, condition7 ; check for right corner ljmp status6;

status6:

mov p2, #08h ;mouse turn right mov p3, #01h mov A, p1 ; read current input from p1 cjne A, #05h, main ljmp status6

condition7:

cjne A, #07h, condition

; check for dead end

status7:

mov p2, #08h ;mouse turn right mov p3, #01h mov A, p1 ; read current input from p1 cjne A, #05h, main ljmp status7 .

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